

BONDING WIRE FOR SEMICONDUCTOR

ABSTRACT

There is provided a bonding wire for semiconductor, capable of ensuring a favorable wedge bondability even when bonded to a palladium-plated lead frame, superior in oxidation resistivity and having a core wire of copper or a copper alloy. This bonding wire comprises: a core wire of copper or a copper alloy; a coating layer containing palladium and having a thickness of 10 to 200nm; and an alloy layer formed on a surface of the coating layer, such alloy layer containing a noble metal and palladium and having a thickness of 1 to 80nm. The aforementioned noble metal is either silver or metal, and a concentration of such noble metal in the alloy layer is not less than 10% and not more than 75% by volume.

No Fig.